AMENDMENTS TO THE CLAIMS

Please **AMEND** claim 1 as shown below.

Please **CANCEL** claims 9-20 without prejudice or disclaimer.

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A light emitting device including a light emitting element and a light sensor for detecting the luminous intensity of the light emitted from the light emitting element,

said light emitting element including a lower electrode, a light emitting material layer including at least a light emitting layer, and an upper electrode having light transparency, which are formed on a substrate in the named order, one of said lower electrode and said upper electrode acting as a cathode, and the other acting as an anode,

at least a portion of said light sensor being formed directly on said upper electrode of said light emitting element.

2. (Canceled)

3. (Previously presented) A light emitting device claimed in Claim 1, wherein light emitting element is an electro-luminescence element.

4. (Original) A light emitting device claimed in Claim 3, wherein said electroluminescence element includes an organic thin film as said light emitting layer included in

said light emitting material layer, said organic thin film has a structure emitting the light in response to an applied current.

5. (Previously presented) A light emitting device claimed in Claim 4, wherein a hole injection and transport layer is provided between said light emitting layer and said anode.

6. (Previously presented) A light emitting device claimed in Claim 5, wherein an electron injection and transport layer is provided between said light emitting layer and said cathode.

7. (Original) A light emitting device claimed in Claim 6, wherein said light sensor includes a pn junction formed by a region formed of a p-type semiconductor and another region formed of an n-type semiconductor.

8. (Original) A light emitting device claimed in Claim 6, wherein said light sensor includes a pin structure formed by a region formed of a p-type semiconductor, another region formed of an n-type semiconductor, and an intrinsic semiconductor sandwiched between those two regions.

9-20. (Canceled)